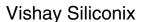
COMPLIANT HALOGEN

FREE





Dual P-Channel 20 V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | | | |
|---------------------|------------------------------------|--------------------|-----------------------|--|--|--|--|--|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) | Q _g (Typ.) | | | | | |
| - 20 | 0.054 at V _{GS} = - 4.5 V | - 4.5 ^a | | | | | | |
| | 0.070 at V _{GS} = - 2.5 V | - 4.5 ^a | 9.5 nC | | | | | |
| | 0.104 at V _{GS} = - 1.8 V | - 4.5 ^a | 9.5110 | | | | | |
| | 0.165 at V _{GS} = - 1.5 V | - 1.5 | | | | | | |

PowerPAK SC-70-6 Dual

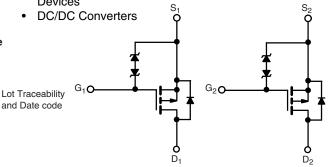
2.05 mm

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection: 2500 V
- 100 % R_q Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

Charger Switches and Load Switches for Portable Devices



Ordering Information: SiA923EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

2.05 mm

P-Channel MOSFET

P-Channel MOSFET

| Parameter | | Symbol | Limit | Unit | | |
|---|-----------------------------------|-----------------|--------------------------|------|--|--|
| Drain-Source Voltage | | V_{DS} | - 20 | V | | |
| Gate-Source Voltage | | V_{GS} | ± 8 | v | | |
| | T _C = 25 °C | | - 4.5 ^a | | | |
| Continuous Drain Current (T _{.I} = 150 °C) | T _C = 70 °C | I _D | - 4.5 ^a | | | |
| Continuous Diam Current (1) = 150 C) | T _A = 25 °C | טי | - 4.5 ^{a, b, c} | | | |
| | T _A = 70 °C | | - 4.5 ^{a, b, c} | A | | |
| Pulsed Drain Current | · | I _{DM} | - 15 | | | |
| Continuous Source-Drain Diode Current | T _C = 25 °C | lo. | - 4.5 ^a | | | |
| Continuous Source-Diam Diode Current | T _A = 25 °C | I _S | - 1.6 ^{b, c} | | | |
| | T _C = 25 °C | | 7.8 | | | |
| Maximum Power Dissipation | T _C = 70 °C | P _D | 5 | w | | |
| Maximum Fower Dissipation | T _A = 25 °C | ' Б | 1.9 ^{b, c} | | | |
| | T _A = 70 °C | | 1.2 ^{b, c} | | | |
| Operating Junction and Storage Temperature R | T _J , T _{stg} | - 55 to 150 | °C | | | |
| Soldering Recommendations (Peak Temperatur | Ĭ | 260 | | | | |

Marking Code

| THERMAL RESISTANCE RATINGS | | | | | | | | | |
|---|--------------|------------|---------|---------|-------|--|--|--|--|
| Parameter | | Symbol | Typical | Maximum | Unit | | | | |
| Maximum Junction-to-Ambient ^{b, f} | t ≤ 5 s | R_{thJA} | 52 | 65 | °C/W | | | | |
| Maximum Junction-to-Case (Drain) | Steady State | R_{thJC} | 12.5 | 16 | O/ VV | | | | |

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See solder profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 110 °C/W.

SiA923EDJ

Vishay Siliconix



| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit | | |
|--|-------------------------|---|-------|-------|-------|---------|--|--|
| Static | - Cymbei | 1991 Conditions | | .,,,, | maxi | - Cilic | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = - 250 μA | - 20 | | | V | | |
| V _{DS} Temperature Coefficient | $\Delta V_{DS}/T_{J}$ | | | - 15 | | mV/°C | | |
| V _{GS(th)} Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | I _D = - 250 μA | | 2.5 | | | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | - 0.5 | | - 1.4 | V | | |
| <u> </u> | | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$ | | ± 0.3 | ± 3 | | | |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$ | | ± 3 | ± 30 | | | |
| | | V _{DS} = - 20 V, V _{GS} = 0 V | | | - 1 | μΑ | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C | | | - 10 | | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$ | - 15 | | | Α | | |
| | (* / | V _{GS} = - 4.5 V, I _D = - 3.8 A | | 0.044 | 0.054 | | | |
| | | V _{GS} = - 2.5 V, I _D = - 3.3 A | | 0.057 | 0.070 | 1 | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = - 1.8 V, I _D = - 1 A | | 0.075 | 0.104 | Ω | | |
| | | V _{GS} = - 1.5 V, I _D = - 0.5 A | | 0.097 | 0.165 | | | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = - 10 V, I _D = - 3.8 A | | 11 | | S | | |
| Dynamic ^b | | | | | | | | |
| | | V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 4.9 A | | 16.3 | 25 | nC | | |
| Total Gate Charge | Q_g | | | 9.5 | 14.5 | | | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.9 \text{ A}$ | | 1.4 | | | | |
| Gate-Drain Charge | Q _{gd} | | | 2.3 | | | | |
| Gate Resistance | R _g | f = 1 MHz | 1 | 5.1 | 10 | Ω | | |
| Turn-On Delay Time | t _{d(on)} | | | 15 | 25 | | | |
| Rise Time | t _r | V_{DD} = - 10 V, R_L = 2.6 Ω | | 16 | 25 | | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong$ - 3.9 A, V_{GEN} = - 4.5 V, R_g = 1 Ω | | 30 | 45 | | | |
| Fall Time | t _f | | | 10 | 15 | | | |
| Turn-On Delay Time | t _{d(on)} | | | 7 | 15 | ns | | |
| Rise Time | t _r | V_{DD} = - 10 V, R_L = 2.6 Ω | | 12 | 20 | | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong$ - 3.9 A, V_{GEN} = - 8 V, R_g = 1 Ω | | 26 | 40 | | | |
| Fall Time | t _f | | | 10 | 15 | | | |
| Drain-Source Body Diode Characterist | ics | | | • | | • | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | - 4.5 | Δ | | |
| lse Diode Forward Current I _{SM} | | | | | - 15 | A | | |
| Body Diode Voltage | V _{SD} | I _S = - 3.9 A, V _{GS} = 0 V | | - 0.9 | - 1.2 | V | | |
| Body Diode Reverse Recovery Time t _{rr} | | | | 13 | 25 | ns | | |
| Body Diode Reverse Recovery Charge | Q _{rr} | I _F = - 3.9 A, dl/dt = 100 A/μs, T _{.I} = 25 °C | | 5.5 | 12 | nC | | |
| Reverse Recovery Fall Time | t _a | $ 1_F = -3.9 \text{ A}, \text{ al/at} = 100 \text{ A/} \mu \text{s}, 1_J = 25 \text{ C}$ | | 7.5 | | ns | | |
| Reverse Recovery Rise Time | t _b | | | 5.5 | | | | |

Notes:

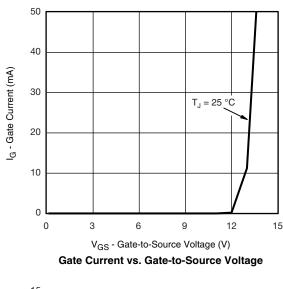
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

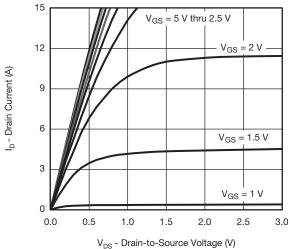
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

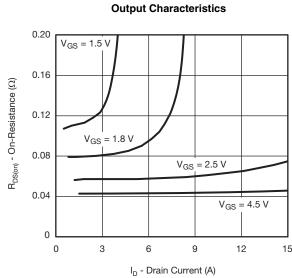
b. Guaranteed by design, not subject to production testing.



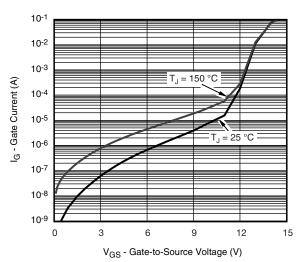
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



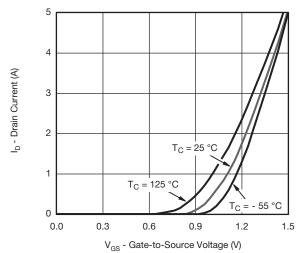




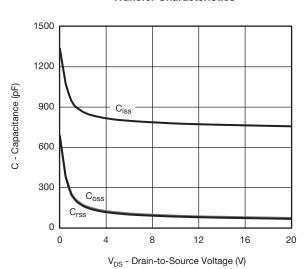




Gate Current vs. Gate-to-Source Voltage



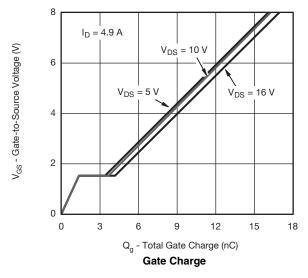
Transfer Characteristics

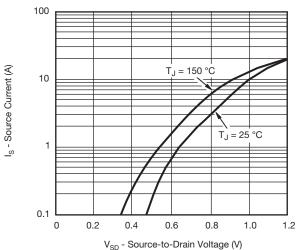


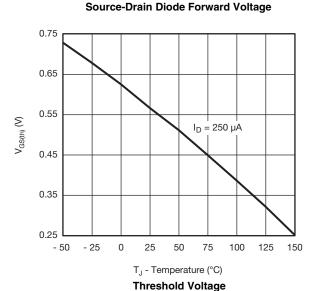
Vishay Siliconix

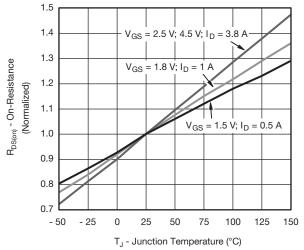
VISHAY.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

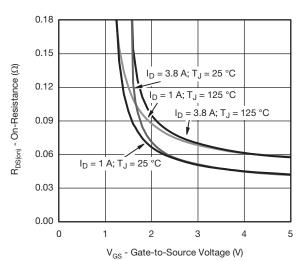




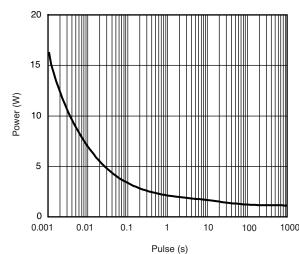




On-Resistance vs. Junction Temperature



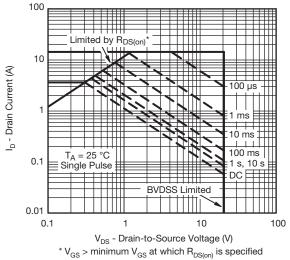
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

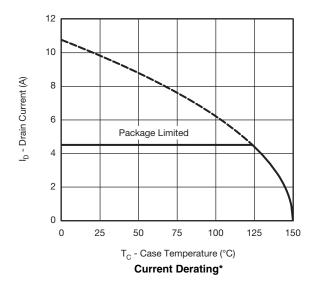


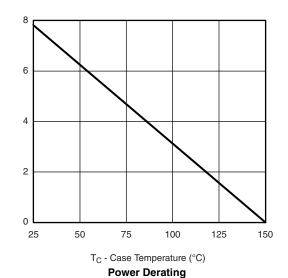
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Safe Operating Area, Junction-to-Ambient

Power Dissipation (W)



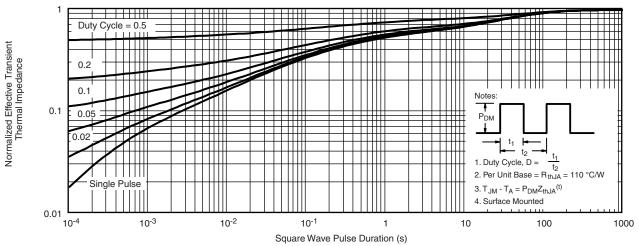


^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package

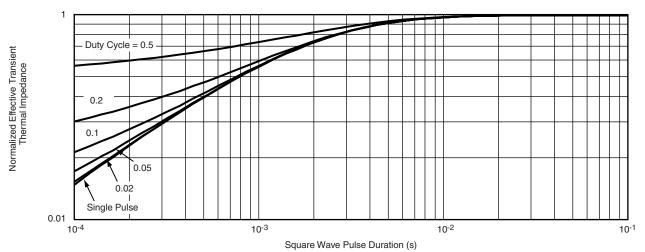
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppq?66803.





Vishay Siliconix

PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

| | SINGLE PAD | | | | | | DUAL PAD | | | | | |
|-----|-------------|---------------------|-----------|---------------------|-----------|-------|-------------|-----------|-------|-----------|-------|-------|
| DIM | MILLIMETERS | | | INCHES | | | MILLIMETERS | | | INCHES | | |
| | Min | Nom | Max | Min | Nom | Max | Min | Nom | Max | Min | Nom | Max |
| Α | 0.675 | 0.75 | 0.80 | 0.027 | 0.030 | 0.032 | 0.675 | 0.75 | 0.80 | 0.027 | 0.030 | 0.032 |
| A1 | 0 | - | 0.05 | 0 | - | 0.002 | 0 | - | 0.05 | 0 | - | 0.002 |
| b | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 |
| С | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| D | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 |
| D1 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 | 0.513 | 0.613 | 0.713 | 0.020 | 0.024 | 0.028 |
| D2 | 0.135 | 0.235 | 0.335 | 0.005 | 0.009 | 0.013 | | | | | | |
| E | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 |
| E1 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 |
| E2 | 0.345 | 0.395 | 0.445 | 0.014 | 0.016 | 0.018 | | | | | | |
| E3 | 0.425 | 0.475 | 0.525 | 0.017 | 0.019 | 0.021 | | | | | | |
| е | | 0.65 BSC | | | 0.026 BSC | ; | 0.65 BSC | | | 0.026 BSC | | |
| K | | 0.275 TYP 0.011 TYP | | 1 | 0.275 TYP | | | 0.011 TYP | | | | |
| K1 | 0.400 TYP | | 0.016 TYP | | 0.320 TYP | | 0.013 TYP | | | | | |
| K2 | 0.240 TYP | | | 0.009 TYP 0.252 TYP | | ı | 0.010 TYP | | | | | |
| К3 | | 0.225 TYP 0.009 TYP | | | | • | | • | • | | | |
| K4 | | 0.355 TYP 0.014 TYP | | | | | | | | | | |
| L | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 |
| T | | | | | | | 0.05 | 0.10 | 0.15 | 0.002 | 0.004 | 0.006 |

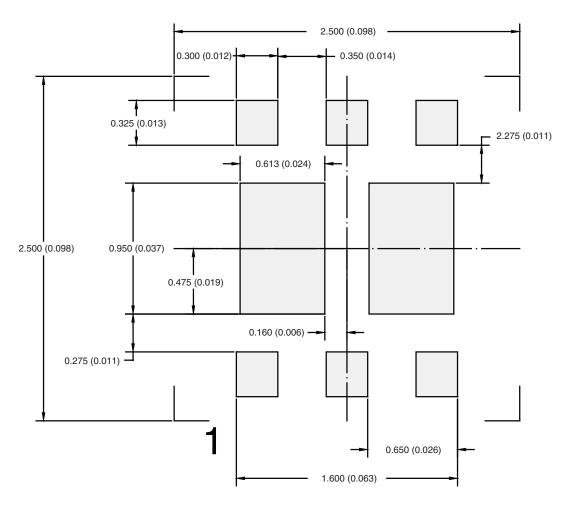
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm/(Inches)

Return to Index



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Revision: 02-Oct-12 Document Number: 91000